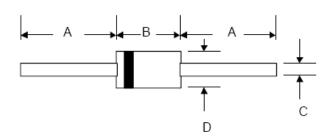
## MR850-MR858 3.0A FAST RECOVERY RECTIFIER

Green Products

Technical Data Data Sheet N0454, Rev. -

#### Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop, High Efficiency
- Low Power Loss
- Fast Recovery Time
- High Surge Current Capability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



### Mechanical Data

- Case: Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type NumberMounting Position: Any
- Weight: 0.21 grams (approx.)

DO-201AD								
Dim	Min	Max	Min	Max				
Α	25.4	_	1.000	_				
В	8.50	9.50	0.335	0.374				
С	1.20	1.30	0.047	0.051				
D	5.0	5.60	0.197	0.220				
All	In mm		In inch					

## **Marking Diagram:**

Where XXXXX is YYWWL



MR850 = Part Name SSG = SSG YY = Year WW = Week L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

### Ordering Information

Device	Package	Shipping		
MR850-MR858	DO-201AD (Pb-Free)	1250pcs / tape		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

<sup>•</sup> Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 🗏 (86) 25-87123907 •

<sup>•</sup> FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •

# MR850-MR858 3.0A FAST RECOVERY RECTIFIER

Technical Data
Data Sheet N0454, Rev. -

**Green Products** 

## Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic	Symbol	MR850	MR851	MR852	MR854	MR856	MR858	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	50	100	200	400	600	800	٧
RMS Reverse Voltage	VR(RMS)	35	70	140	280	420	560	٧
Average Rectified Output Current @T <sub>L</sub> = 75°C	lo	3.0					Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	150					А	
Forward Voltage @I F = 3.0A	VFM	1.25 1.30					٧	
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 100°C	lRM	10 200				μΑ		
Reverse Recovery Time (Note 1)	trr	100 150			50	nS		
Typical Junction Capacitance (Note 2)	G	80					pF	
Operating and Storage Temperature Range	Тј, Тѕтс	-65 to +150				°C		

Note: 1. Measured with  $I_F = 0.5A$ ,  $I_R = 1.0A$ ,  $I_{T} = 0.25A$ ,

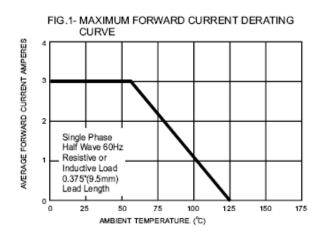
<sup>2.</sup> Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

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### RATINGS AND CHARACTERISTIC CURVES (MR850-MR858)



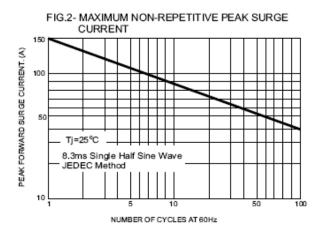


FIG.3- TYPICAL FORWARD CHARACTERISTICS

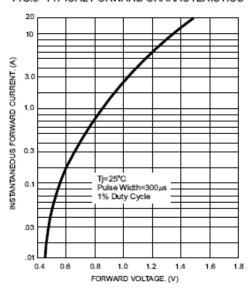


FIG.4- TYPICAL JUNCTION CAPACITANCE

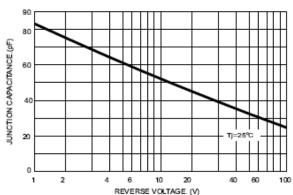
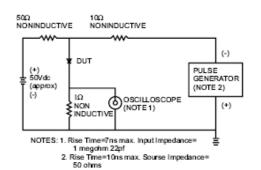
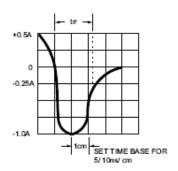


FIG.5- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM





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## MR850-MR858 3.0A FAST RECOVERY RECTIFIER

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